

Resource Summary Report

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Texas State University PECVD System

RRID:SCR_028202

Type: Tool

Proper Citation

Texas State University PECVD System (RRID:SCR_028202)

Resource Information

URL: <https://sro.txst.edu/sro-facilities/sro-nrsc/sro-nrsc-pecvd.html>

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Description: Facility plasma-enhanced chemical vapor deposition (PECVD) system from AGS utilizes plasma decomposition of silane (SiH_4) in presence of an oxygen or nitrogen source to deposit SiO_2 and Si_3N_4 dielectric thin films. The capacitive coupled plasma reduces the required temperature for deposition to a minimum of $\sim 150^\circ\text{C}$. A plasma-enhanced chemical vapor deposition system is used to deposit high-quality thin films at reduced temperatures for semiconductor and materials applications.

Synonyms: , PECVD System (Versaline PECVD), Plasma-Enhanced Chemical Vapor Deposition system

Resource Type: instrument resource

Keywords: PECVD, plasma deposition, thin films, dielectric layers, semiconductor

Availability: Restricted

Resource Name: Texas State University PECVD System

Resource ID: SCR_028202

Alternate URLs:

<https://asrc.gc.cuny.edu/facilities/nanofabrication/instruments/deposition/>,
<https://sro.txst.edu/sro-facilities/sro-nrsc.html>

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Ratings and Alerts

No rating or validation information has been found for Texas State University PECVD System.

No alerts have been found for Texas State University PECVD System.

Data and Source Information

Source: [SciCrunch Registry](#)

Usage and Citation Metrics

We have not found any literature mentions for this resource.